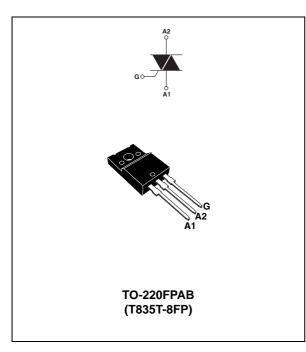


#### 8 A Snubberless™ Triac

Datasheet - production data



**Table 1. Device summary** 

Symbol	Value	Unit
I <sub>T(rms)</sub>	8	Α
$V_{DRM}, V_{RRM}$	800	V
$V_{DSM}, V_{RSM}$	900	V
I <sub>GT</sub>	35	mA

#### **Features**

- Medium current Triac
- High static and dynamic commutation
- Three quadrants
- ECOPACK<sup>®</sup>2 compliant component
- Complies with UL standards (File ref: E81734)

### **Applications**

- · General purpose AC line load switching
- Motor control circuits
- Small home appliances
- Lighting
- · Inrush current limiting circuits
- Overvoltage crowbar protection

#### **Description**

Available in through-hole full pack package, the T835T-8FP Triac can be used for the on/off or phase angle control function in general purpose AC switching where high commutation capability is required. This device can be used without a snubber circuit when the limits defined in this datasheet are respected

Provides UL certified insulation rated at 1500 V rms.

TM: Snubberless is a trademark of STMicroelectronics

Characteristics T835T-8FP

## 1 Characteristics

Table 2. Absolute maximum ratings ( $T_j = 25$  °C unless otherwise stated)

Symbol	Paramete	Value	Unit		
I <sub>T(rms)</sub>	On-state rms current (full sine wave	T <sub>c</sub> = 113°C	8	Α	
l	Non repetitive surge peak on-state	F = 50 Hz	t = 20 ms	60	А
I <sub>TSM</sub>	current (full cycle, T <sub>j</sub> initial = 25 °C)	F = 60 Hz	t = 16.7 ms	63	Α
l <sup>2</sup> t	I <sup>2</sup> t value for fusing, T <sub>j</sub> initial = 25 °C		$t_p = 10 \text{ ms}$	24	A <sup>2</sup> s
V <sub>DRM</sub> ,	Popotitivo curgo poak off stato volta		T <sub>j</sub> = 150 °C	600	V
$V_{RRM}$	Repetitive surge peak off-state voltage		T <sub>j</sub> = 125 °C	800	V
V <sub>DSM</sub> , V <sub>RSM</sub>	Non repetitive surge peak off-state v	t <sub>p</sub> = 10 ms	900	V	
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ , $t_r \le 100 \text{ ns}$	I F = 100 Hz		100	A/µs
I <sub>GM</sub>	Peak gate current	t <sub>p</sub> = 20 μs	T <sub>j</sub> = 150 °C	4	Α
P <sub>G(AV)</sub>	Average gate power dissipation	1	W		
T <sub>stg</sub>	Storage junction temperature range			- 40 to + 150 - 40 to + 150	°C
T <sub>j</sub>	Operating junction temperature rang				
T <sub>L</sub>	Maximum lead temperature for sold	260	°C		
V <sub>ins</sub>	Insulation rms voltage, 1 minute	1500	V		

Table 3. Electrical characteristics ( $T_j = 25$  °C, unless otherwise stated)

Symbol	Test conditions Quadrant			Value	Unit
I <sub>GT</sub> <sup>(1)</sup>	(1)		Min.	1.75	A
'GT`	$V_D = 12 \text{ V}, R_L = 30 \Omega$	1 - 11 - 111	Max.	35	mA
V <sub>GT</sub>	$V_D$ = 12 V, $R_L$ = 30 $\Omega$	1 - 11 - 111	Max.	1.3	V
V <sub>GD</sub>	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega, T_j = 150 \text{ °C}$	1 - 11 - 111	Min.	0.2	V
I <sub>H</sub> <sup>(1)</sup>	I <sub>T</sub> = 500 mA		Max.	40	mA
	I <sub>G</sub> = 1.2 I <sub>GT</sub>	1 - 111	Max.	60	mA
IL		II	Max.	65	mA
dV/dt <sup>(1)</sup>	V <sub>D</sub> = 536 V, gate open	T <sub>j</sub> = 125 °C	Min.	2000	V/µs
u v/ut · /	V <sub>D</sub> = 402 V, gate open	T <sub>j</sub> = 150 °C	IVIII I.	1000	V/µs
(dl/dt)c (1)	Mith and are the are (all (lab) and 20 Mina)	T <sub>j</sub> = 125 °C	Min.	8	A/ms
(ai/at)c (1)	Without snubber (dV/dt)c ≥ 20 V/µs)	T <sub>j</sub> = 150 °C	IVIII I.	4	

<sup>1.</sup> For both polarities of A2 referenced to A1

T835T-8FP Characteristics

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Iabic	<b></b> -	Static	Guara	LICHSHLS

Symbol	Test conditions			Value	Unit
V <sub>T</sub> <sup>(1)</sup>	$I_{TM} = 11.3 \text{ A}, t_p = 380  \mu\text{s}$	T <sub>j</sub> = 25 °C	Max.	1.55	V
V <sub>t0</sub> (1)	Threshold voltage	T <sub>j</sub> = 150 °C	Max.	0.85	V
R <sub>d</sub> <sup>(1)</sup>	Dynamic resistance	T <sub>j</sub> = 150 °C	Max.	57	mΩ
	$V_{DRM} = V_{RRM} = 800 \text{ V}$ $T_j = 25 \text{ °C}$ $T_j = 125 \text{ °C}$	Max.	5	μΑ	
I <sub>DRM</sub>		T <sub>j</sub> = 125 °C	iviax.	0.8	m 1
'KKW	V <sub>DRM</sub> = V <sub>RRM</sub> = 600 V	T <sub>j</sub> = 150 °C	Max.	2.4	mA

<sup>1.</sup> For both polarities of A2 referenced to A1

**Table 5. Thermal resistance** 

Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>	Junction to case (AC)	3.8	°C/W
R <sub>th(j-a)</sub>	Junction to ambient (DC)	60	°C/W

Figure 1. Maximum power dissipation versus on-state rms current (full cycle)

Figure 2. On-state rms current versus case temperature (full cycle)

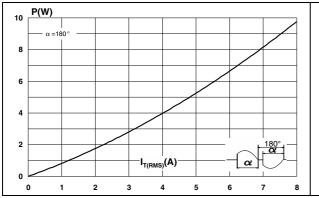
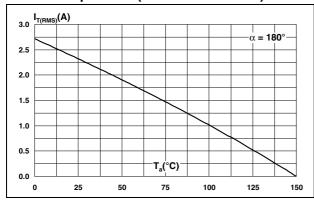
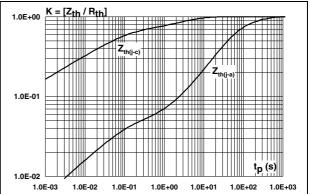


Figure 3. On-state rms current versus ambient temperature (free air convection)

Figure 4. Relative variation of thermal impedance versus pulse duration

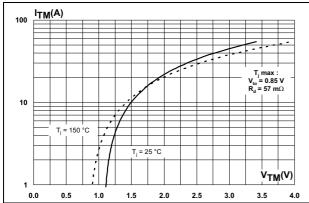




Characteristics T835T-8FP

Figure 5. On-state characteristics (maximum values)

Figure 6. Surge peak on-state current versus number of cycles



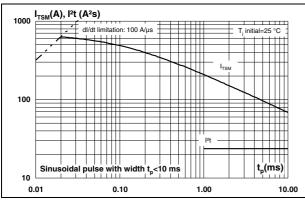
70 | TSM(A)

60 | TSM(A)

10 |

Figure 7. Non repetitive surge peak on-state current and corresponding values of I<sup>2</sup>t

Figure 8. Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)



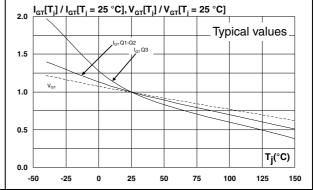
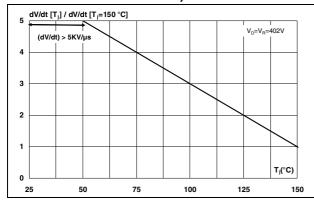
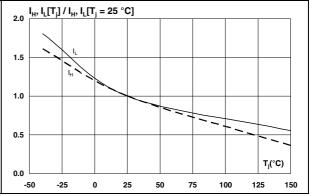


Figure 9. Relative variation of static dV/dt immunity versus junction temperature (typical values)

Figure 10. Relative variation of holding and latching current versus junction temperature (typical values)





T835T-8FP Characteristics

Figure 11. Relative variation of critical rate of decrease of main current (di/dt)c versus reapplied (dV/dt)c (typical values)

Figure 12. Relative variation of critical rate of decrease of main current (di/dt)c versus junction temperature (typical values)

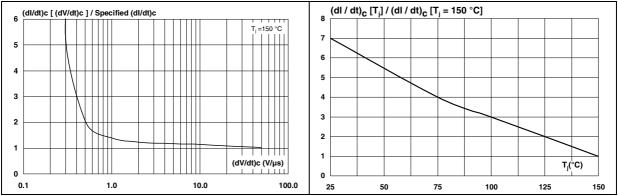
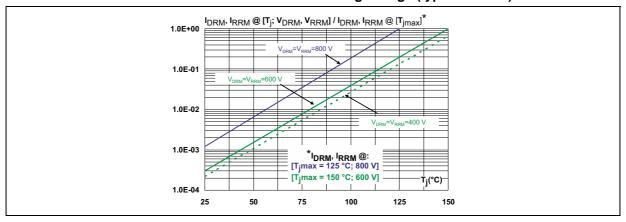


Figure 13. Relative variation of leakage current versus junction temperature for different values of blocking voltage (typical values)



Package information T835T-8FP

## 2 Package information

- Epoxy meets UL94, V0
- Lead-free package
- Recommended torque: 0.4 to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

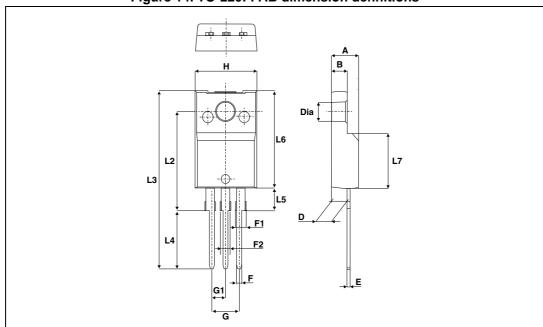


Figure 14. TO-220FPAB dimension definitions

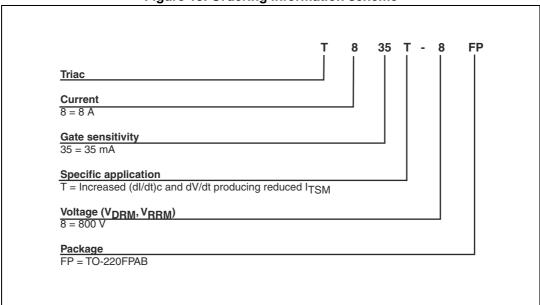
Table 6. TO-220FPAB dimension values

	Dimensions					
Ref.	Millin	Millimeters		hes		
	Min.	Max.	Min.	Max.		
А	4.4	4.6	0.173	0.181		
В	2.5	2.7	0.098	0.106		
D	2.5	2.75	0.098	0.108		
E	0.45	0.70	0.018	0.027		
F	0.75	1	0.030	0.039		
F1	1.15	1.70	0.045	0.067		
F2	1.15	1.70	0.045	0.067		
G	4.95	5.20	0.195	0.205		
G1	2.4	2.7	0.094	0.106		
Н	10	10.4	0.393	0.409		
L2	16 <sup>-</sup>	Тур.	0.63	Тур.		
L3	28.6	30.6	1.126	1.205		
L4	9.8	10.6	0.386	0.417		
L5	2.9	3.6	0.114	0.142		
L6	15.9	16.4	0.626	0.646		
L7	9.00	9.30	0.354	0.366		
Dia.	3.00	3.20	0.118	0.126		

Ordering information T835T-8FP

# 3 Ordering information

Figure 15. Ordering information scheme



**Table 7. Ordering information** 

Order code	Marking	Package	Weight	Base qty	Delivery mode
T835T-8FP	T835T-8FP	TO-220FPAB	2.0 g	50	Tube

## 4 Revision history

Table 8. Document revision history

Date	Revision	Changes
05-Mar-2013	1	Initial release.

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